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Gwun J. Cantrell

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group Art Unit: 2813

122 M

In re Patent application of:

Shunpei YAMAZAKI et al.

Serial No.: 09/437,135

Examiner: E. Kielin Filed: November 10, 1999

SEMICONDUCTOR DEVICE AND For:

METHOD FOR FORMING THE SAME)

AMENDMENT AFTER FINAL REJECTION

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

Responsive to the Office Action dated September 17, 2001, the following amendments and remarks are submitted in connection with the above-identified application.

IN THE CLAIMS:

Please amended claims 1, 6, 11, 30, and 34 as follows. Attached hereto is a marked up copy of the claims in their amended form.

(Thrice Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film comprising amorphous silicon over a substrate; crystallizing said seniconductor film by irradiating a laser light;

patterning the crystallized semiconductor film to form first and second semiconductor islands;

forming an insulating film of each of said first and second semiconductor islands by a vapor phase deposition;

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